

Vishay Siliconix

P-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^d	Q _g (Typ.)		
- 60	0.019 at V _{GS} = - 10 V	- 55	76		
- 60	0.025 at V _{GS} = - 4.5 V	- 48	70		

FEATURES

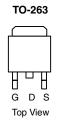
• TrenchFET[®] Power MOSFET

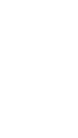
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P-Channel MOSFET







Ordering Information: SUM55P06-19L SUM55P06-19L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T_{C}	= 25 °C, unless other	wise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	- 60	v		
Gate-Source Voltage	V _{GS}	± 20	v		
Continuous Durin Connect ^d (T. 175 °C)	T _C = 25 °C	L	- 55	•	
Continuous Drain Current ^d ($T_J = 175 \ ^{\circ}C$)	T _C = 125 °C	I _D	- 31		
Pulsed Drain Current	I _{DM}	- 150	A		
Avalanche Current	L = 0.1 mH	I _{AS}	- 45		
Single Pulse Avalanche Energy ^a		E _{AS}	101	mJ	
Devery Directory	T _C = 25 °C	Р	125 ^c	w	
Power Dissipation	T _A = 25 °C ^b	P _D	3.75		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Limit	Unit		
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	40	°C/W		
Junction-to-Case		R _{thJC}	1.2	0/10		

Notes:

a. Duty cycle \leq 1%.

b. When Mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

d. Limited by package.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

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SPECIFICATIONS T _J = 25 ° Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static	Symbol	Test conditions	IVIIII.	Typ.	wax.	Unit	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 250 μA	- 60				
Gate-Threshold Voltage	V _{GS(th)}				- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	- 1		± 100	nA	
	.035	$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	-	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 \text{ °C}$			- 50	μA	
	.033	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 175 ^{\circ}\text{C}$			- 250	- ^µ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	- 120			A	
	D(01)	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -30 \text{ A}$		0.015	0.019		
		$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -30 \text{ A}, \text{ T}_{J} = 125 \text{ °C}$		0.0.0	0.033	033 Ω	
Drain-Source On-State Resistance ^a	r _{DS(on)}	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -30 \text{ A}, \text{ T}_{J} = 175 \text{ °C}$			0.041		
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -20 \text{ A}$		0.020	0.025	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 50 A	20			S	
Dynamic ^b	013	50 , 5					
Input Capacitance	C _{iss}			3500		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		390			
Reverse Transfer Capacitance	C _{rss}			290			
Total Gate Charge ^c	Qq			76	115		
Gate-Source Charge ^c	Q _{gs}	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 55 A		16		nC	
Gate-Drain Charge ^c	Q _{gd}			19			
Gate Resistance	R _a	f = 1.0 MHz		5.2		Ω	
Turn-On Delay Time ^c	t _{d(on)}			12	20		
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, \text{ R}_1 = 0.54 \Omega$		15	25	- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -55 \text{ A}, V_{\text{GEN}} = -10 \text{ V}, R_{\text{g}} = 2.5 \Omega$		80	120		
Fall Time ^c	t _f			230	350		
Source-Drain Diode Ratings and Cha	· ·	- 25 °Cb		200	000		
	1	C = 23 C		1	110		
Continuous Current	I _S				- 110	А	
Pulsed Current	I _{SM}	I _F = - 50 A, V _{GS} = 0 V		10	- 240		
Forward Voltage ^a	V _{SD}	$I_{F} = -50 \text{ A}, V_{GS} = 0 \text{ V}$		- 1.0	- 1.5	V	
Reverse Recovery Time	t _{rr}	L = 50 A di/dt 100 A/va		45	68	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 50 A, di/dt = 100 A/μs		- 2.6	4.0	A	
Reverse Recovery Charge	Q _{rr}			0.059	0.136	μC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

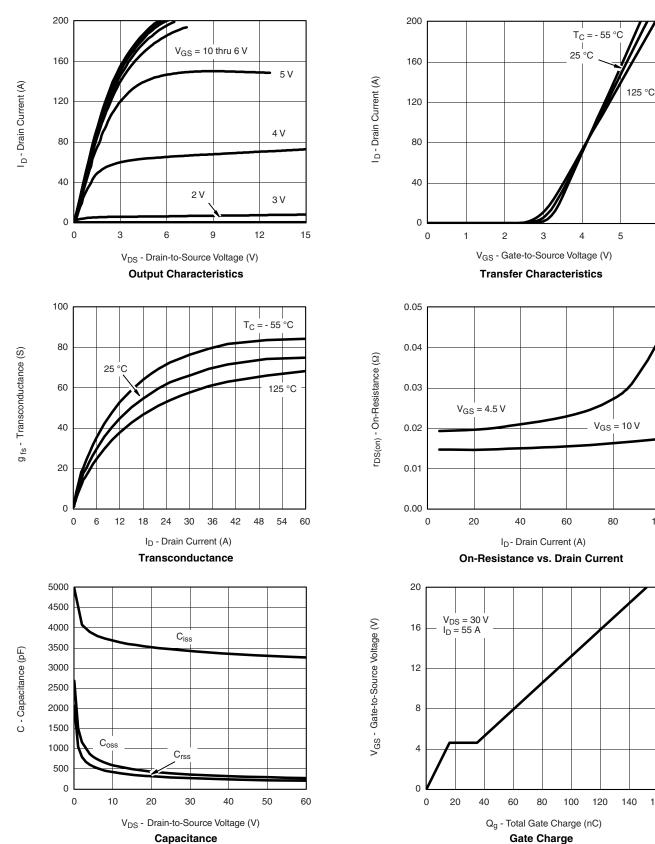


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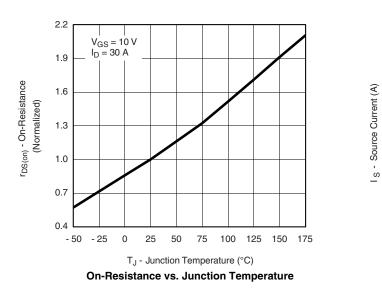
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

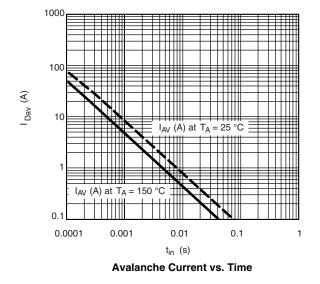
Document Number: 73059 S-80272-Rev. C, 11-Feb-08 160

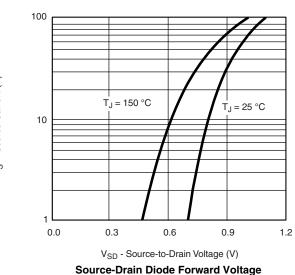
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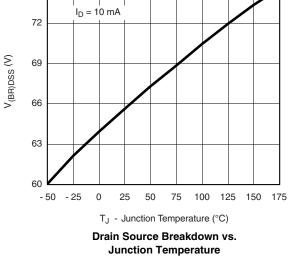


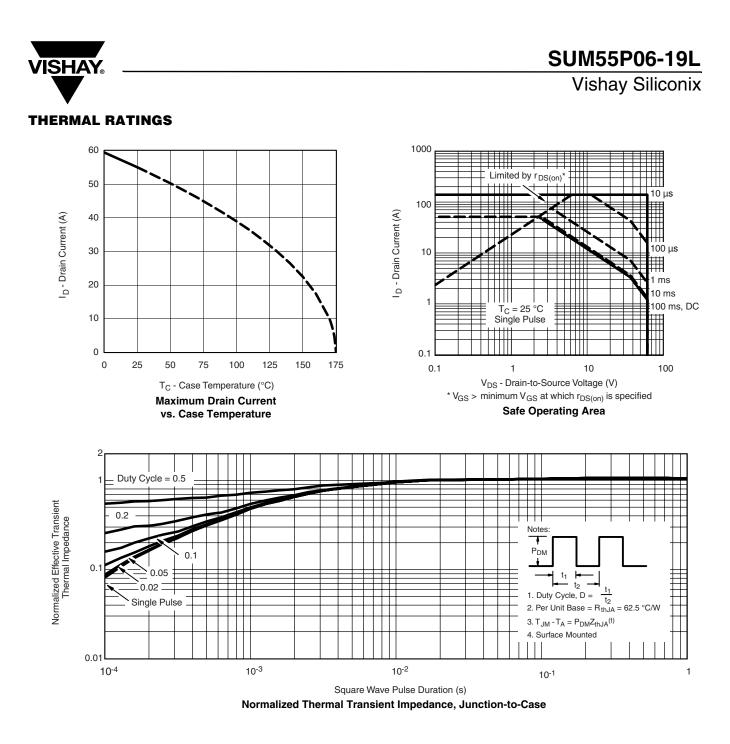




I_D = 10 mA

75



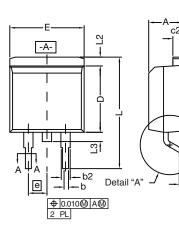


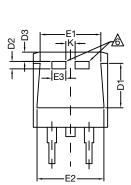


Package Information

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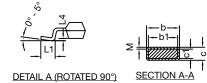
TO-263 (D²PAK): 3-LEAD





-B-

С



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
	А	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017 9.525		
	E3	0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54	BSC	
	К	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	- 0.050		
ECN: T10-0738-Rev. J, 03-Jan-11 DWG: 5843						

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
- Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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